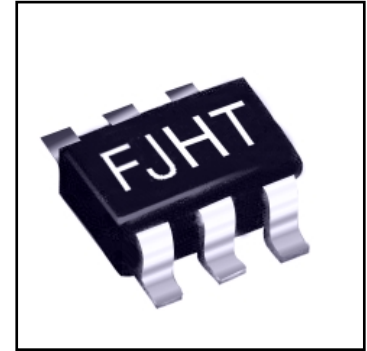


FEATURES

- Low Power Consumption: 60mW (Typ.)
- Operation to 6.0 GHz
- Input Frequency divide by 4, OUT and $\overline{\text{OUT}}$
- -3V (or+3V) DC Single Power Supply
- External 50 ohm Load Driving Capability
- Small 6-pin **Plastic** Package for SMT applications (ML)
- Tape and Reel available



DESCRIPTION

The FMM1062ML is a GaAs Microwave Static Frequency Divider designed for dividing an input signal by 4 over a frequency range from 2.0 to 6.0 GHz. This part is designed for Synthesizer, Phase-Locked Oscillator, Electronic Toll Collection (ETC) applications.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATINGS (Ambient Temperature Ta=25°C)

Parameter	Symbol	Limit		Unit
		Min.	Max.	
Supply Voltage	V _{DD}	-0.5	+4.5	V
Input Voltage	I _{DD}	-	40	mA
Input Voltage	V _{in}	-0.5	V _{DD} to +0.5	V
Input Power	P _{in}	-	+13.0	dBm
Storage Temperature	T _{stg}	-65	+150	°C
Power Dissipation	P _D	-	0.12	W

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Limit			Unit
		Min.	Typ.	Max.	
Supply Voltage	V _{DD}	+2.7	+3.0	+3.6	V
Ambient Temperature	T _a	-40	-	+85	°C

ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta = -40~+85°C, VDD = +2.7~+3.6V)

Parameter	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Power Supply Current	I _{DD}	V _{DD} = 3.0V, T _a = 25°C	-	21.0	-	mA
Output Power	P _{out}	R _L = 50Ω, f _{in} = 5.8 GHz	-8	-4	0	dBm
Operating Frequency	f _{in}	P _{in} = 0dBm	2.0	-	6.0	GHz
Input Power	P _{in}	f _{in} = 2~6 GHz	-5	0	+10	dBm

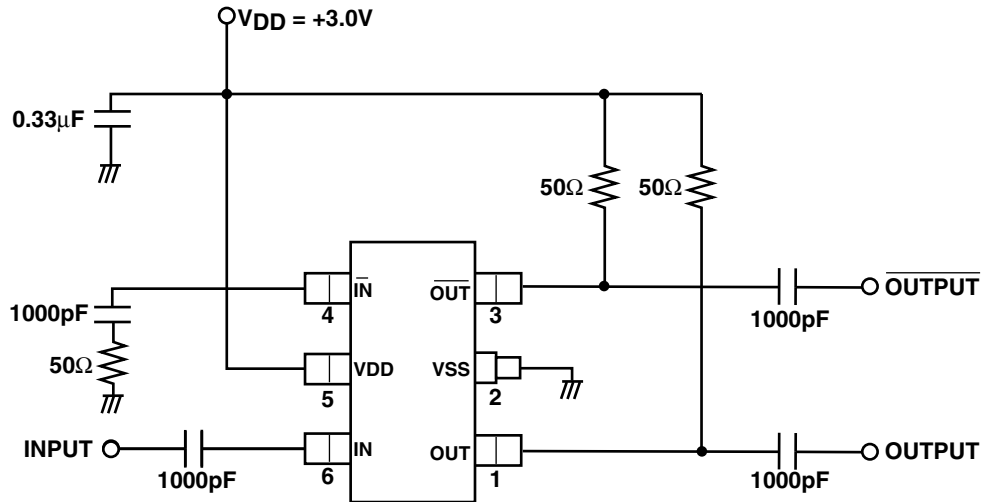
CASE STYLE: ML

1. Electrical characteristics are assured on a lot basis by sample testing at an AQL = 0.1%, Level II. Any lot failure shall be 100% retested.
2. The package marking "FJHT" shows the part number, year and month of manufacturer.

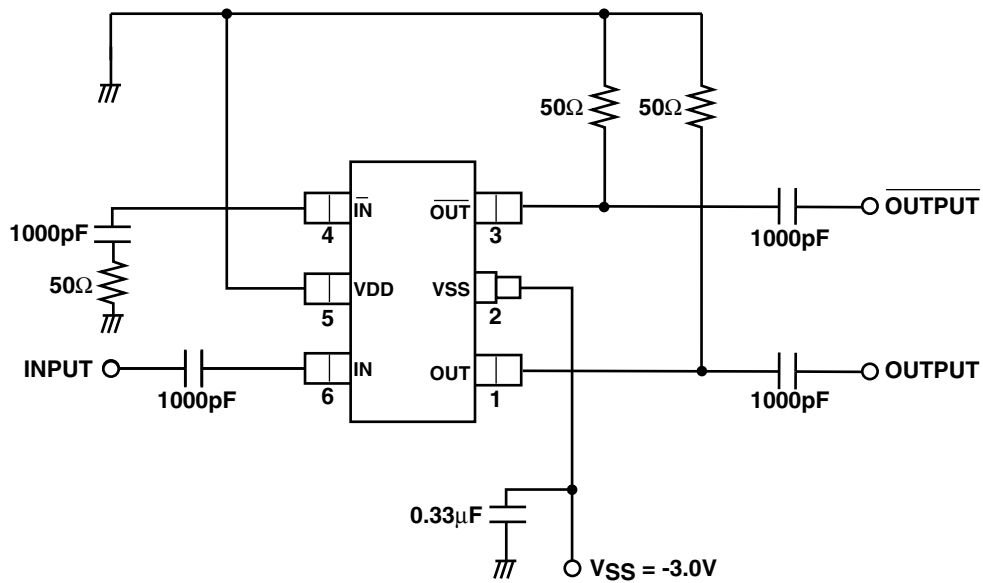
Where: "FJ" indicates the part number (FMM1062ML)
 "H" indicates the year (2000)
 "T" indicates the month (July)

Test Circuit

Positive Supply Voltage
VDD = +3V Operation Circuit



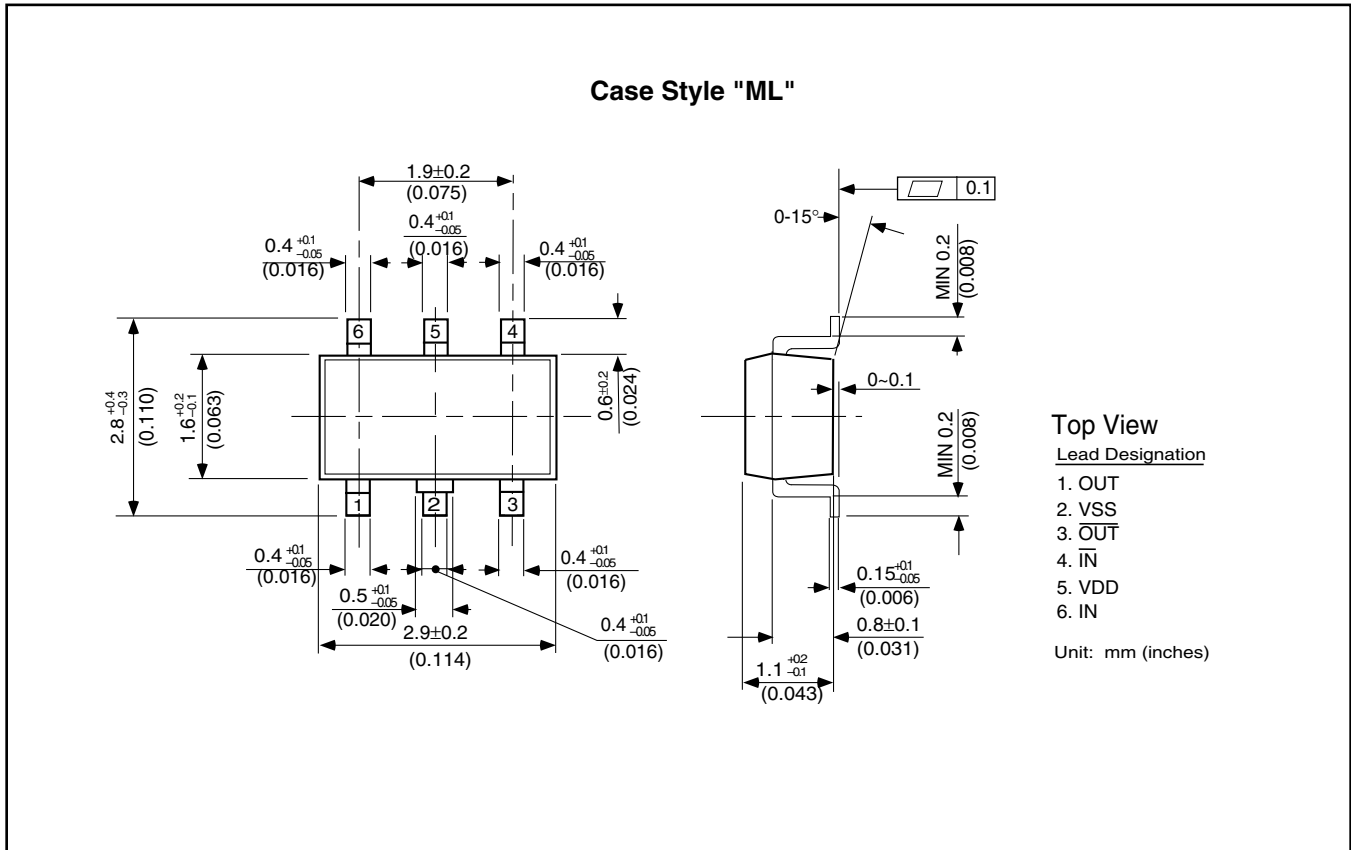
Negative Supply Voltage
VSS = -3V Operation Circuit



NOTES

FMM1062ML

GaAs MMIC



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